Martin Albrecht

List of Publications by Year
in descending order

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276	10,183	34100 52	43886 91
papers	citations	h-index	g-index

286	286	286	8635
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Catalytic Activity of Faceted Gold Nanoparticles Studied by a Model Reaction: Evidence for Substrate-Induced Surface Restructuring. ACS Catalysis, 2011, 1, 908-916.	11.2	504
2	Defect structure of epitaxial GaN films determined by transmission electron microscopy and triple-axis X-ray diffractometry. Philosophical Magazine A: Physics of Condensed Matter, Structure, Defects and Mechanical Properties, 1998, 77, 1013-1025.	0.6	498
3	Grating-Coupling of Surface Plasmons onto Metallic Tips:â€‰ A Nanoconfined Light Source. Nano Letters, 2007, 7, 2784-2788.	9.1	468
4	Czochralski growth and characterization of Î²â€Ga₂O₃ single crystals. Crystal Research and Technology, 2010, 45, 1229-1236.	1.3	378
5	Rapid carrier relaxation in self-assembledInxGa1âˆ’xAs/GaAs quantum dots. Physical Review B, 1996, 54, 11532-11538.	3.2	289
6	High-voltage field effect transistors with wide-bandgap Î²-Ga2O3 nanomembranes. Applied Physics Letters, 2014, 104, .	3.3	288
7	Systematic experimental and theoretical investigation of intersubband absorption inGaNâˆ•AlNquantum wells. Physical Review B, 2006, 73, .	3.2	239
8	Editors' Choiceâ€”Si- and Sn-Doped Homoepitaxial Î²-Ga₂O₃Layers Grown by MOVPE on (010)-Oriented Substrates. ECS Journal of Solid State Science and Technology, 2017, 6, Q3040-Q3044.	1.8	219
9	Strained state of Ge(Si) islands on Si: Finite element calculations and comparison to convergent beam electronâ€diffraction measurements. Applied Physics Letters, 1994, 64, 3617-3619.	3.3	184
10	Homoepitaxial growth of Î²â€Ga₂O₃ layers by metalâ€organic vapor phase epitaxy. Physica Status Solidi (A) Applications and Materials Science, 2014, 211, 27-33.	1.8	170
11	State of Transition Metal Catalysts During Carbon Nanotube Growth. Journal of Physical Chemistry C, 2009, 113, 1648-1656.	3.1	166
12	GaN/AlN short-period superlattices for intersubband optoelectronics: A systematic study of their epitaxial growth, design, and performance. Journal of Applied Physics, 2008, 104, 093501.	2.5	165
13	Electrical compensation by Ga vacancies in Ga2O3 thin films. Applied Physics Letters, 2015, 106, .	3.3	142
14	Properties of rare-earth scandate single crystals (Re=Ndâˆ’Dy). Journal of Crystal Growth, 2008, 310, 2649-2658.	1.5	137
15	Structural properties of Si-doped Î²-Ga2O3 layers grown by MOVPE. Journal of Crystal Growth, 2014, 401, 665-669.	1.5	133
16	Microstructure of novel superhard nanocrystalline-amorphous composites as analyzed by high resolution transmission electron microscopy. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1998, 16, 19.	1.6	116
17	Semiconducting Sn-doped Î²-Ga2O3 homoepitaxial layers grown by metal organic vapour-phase epitaxy. Journal of Materials Science, 2016, 51, 3650-3656.	3.7	116
18	Strain Induced Deep Electronic States around Threading Dislocations in GaN. Physical Review Letters, 2004, 93, 196401.	7.8	107

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19	Tailoring the graphene/silicon carbide interface for monolithic wafer-scale electronics. Nature Communications, 2012, 3, 957.	12.8	106
20	Surface ripples, crosshatch pattern, and dislocation formation: Cooperating mechanisms in lattice mismatch relaxation. Applied Physics Letters, 1995, 67, 1232-1234.	3.3	105
21	Epitaxial stabilization of pseudomorphic Î±-Ga₂O₃on sapphire (0001). Applied Physics Express, 2015, 8, 011101.	2.4	104
22	Cathodoluminescence spectroscopy of epitaxial-lateral-overgrown nonpolar (11-20) and semipolar (11-22) GaN in relation to microstructural characterization. Journal of Applied Physics, 2007, 101, 113101.	2.5	99
23	Phonons as probes in self-organized SiGe islands. Applied Physics Letters, 1997, 71, 3856-3858.	3.3	98
24	Stacking Faults as Quantum Wells for Excitons in Wurtzite GaN. Physica Status Solidi A, 1997, 164, 141-144.	1.7	98
25	On the nature and temperature dependence of the fundamental band gap of In₂O₃. Physica Status Solidi (A) Applications and Materials Science, 2014, 211, 54-58.	1.8	96
26	Polarity Control in Group-III Nitrides beyond Pragmatism. Physical Review Applied, 2016, 5, .	3.8	94
27	Effect of annealing on the In and N distribution in InGaAsN quantum wells. Applied Physics Letters, 2002, 81, 2719-2721.	3.3	86
28	Cathodoluminescence and Transmission Electron Microscopy Study of the Influence of Crystal Defects on Optical Transitions in GaN. Physica Status Solidi A, 1999, 171, 325-339.	1.7	83
29	Kinetic analysis of the reduction of 4-nitrophenol catalyzed by Au/Pd nanoalloys immobilized in spherical polyelectrolyte brushes. Physical Chemistry Chemical Physics, 2015, 17, 28137-28143.	2.8	83
30	Doping of Czochralski-grown bulk Î²-Ga2O3 single crystals with Cr, Ce and Al. Journal of Crystal Growth, 2018, 486, 82-90.	1.5	83
31	Carrier recombination at single dislocations in GaN measured by cathodoluminescence in a transmission electron microscope. Journal of Applied Physics, 2002, 92, 2000-2005.	2.5	82
32	Substrate-orientation dependence of Î²-Ga2O3 (100), (010), (001), and (2Â¯01) homoepitaxy by indium-mediated metal-exchange catalyzed molecular beam epitaxy (MEXCAT-MBE). APL Materials, 2020, 8, .	5.1	80
33	Si-doped GaNâˆ•AlN quantum dot superlattices for optoelectronics at telecommunication wavelengths. Journal of Applied Physics, 2006, 100, 044326.	2.5	77
34	Evolution of planar defects during homoepitaxial growth of Î²-Ga2O3 layers on (100) substratesâ€"A quantitative model. Journal of Applied Physics, 2016, 120, .	2.5	75
35	Nonradiative recombination at threading dislocations in n-type GaN: Studied by cathodoluminescence and defect selective etching. Applied Physics Letters, 2008, 92, .	3.3	74
36	Ultra-wide bandgap, conductive, high mobility, and high quality melt-grown bulk ZnGa2O4 single crystals. APL Materials, 2019, 7, .	5.1	74

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37	Catalytic activity of nanoalloys from gold and palladium. Physical Chemistry Chemical Physics, 2012, 14, 6487.	2.8	73
38	Step-flow growth in homoepitaxy of Î²-Ga2O3 (100)â€"The influence of the miscut direction and faceting. APL Materials, 2019, 7, .	5.1	73
39	Pinholes, Dislocations and Strain Relaxation in InGaN. MRS Internet Journal of Nitride Semiconductor Research, 1998, 3, 1.	1.0	72
40	Highâ€Outputâ€Power Ultraviolet Light Source from Quasiâ€2D GaN Quantum Structure. Advanced Materials, 2016, 28, 7978-7983.	21.0	72
41	Reduced effective misfit in laterally limited structures such as epitaxial islands. Applied Physics Letters, 1995, 66, 574-576.	3.3	71
42	Temperature-dependent thermoelectric properties of individual silver nanowires. Physical Review B, 2015, 91, .	3.2	69
43	Influence of incoherent twin boundaries on the electrical properties of Î²-Ga2O3 layers homoepitaxially grown by metal-organic vapor phase epitaxy. Journal of Applied Physics, 2017, 122, .	2.5	69
44	Solid-phase crystallized Si films on glass substrates for thin film solar cells. Solar Energy Materials and Solar Cells, 1997, 46, 147-155.	6.2	68
45	Blocking Growth by an Electrically Active Subsurface Layer: The Effect of Si as an Antisurfactant in the Growth of GaN. Physical Review Letters, 2013, 110, 036103.	7.8	66
46	Simultaneous experimental evaluation of In and N concentrations in InGaAsN quantum wells. Journal of Applied Physics, 2001, 90, 3792-3798.	2.5	65
47	Melt growth, characterization and properties of bulk In2O3 single crystals. Journal of Crystal Growth, 2013, 362, 349-352.	1.5	62
48	Diamond nucleation under bias conditions. Journal of Applied Physics, 1998, 83, 531-539.	2.5	60
49	Step flow growth of Î²-Ga2O3 thin films on vicinal (100) Î²-Ga2O3 substrates grown by MOVPE. Applied Physics Letters, 2020, 116, .	3.3	59
50	MgGa₂ O₄ as a new wide bandgap transparent semiconducting oxide: growth and properties of bulk single crystals. Physica Status Solidi (A) Applications and Materials Science, 2015, 212, 1455-1460.	1.8	56
51	Short-wavelength intersubband electroabsorption modulation based on electron tunneling between GaNâ•AlN coupled quantum wells. Applied Physics Letters, 2007, 90, 223511.	3.3	54
52	Chemically orderedAlxGa1â^'xNalloys:â€ƒSpontaneous formation of natural quantum wells. Physical Review B, 2005, 71, .	3.2	53
53	Faceting and metal-exchange catalysis in (010) Î²-Ga2O3 thin films homoepitaxially grown by plasma-assisted molecular beam epitaxy. APL Materials, 2019, 7, .	5.1	53
54	From CaSi2 to siloxene: epitaxial silicide and sheet polymer films on silicon. Journal of Crystal Growth, 1999, 203, 570-581.	1.5	51

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55	Interfacial Energies Providing a Driving Force for Ge/Si Heteroepitaxy. Physical Review Letters, 1994, 73, 444-447.	7.8	49
56	Vertical transport in group III-nitride heterostructures and application in AlN/GaN resonant tunneling diodes. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 2210-2227.	0.8	49
57	Ultraviolet luminescence in AlN. Physica Status Solidi (B): Basic Research, 2011, 248, 1513-1518.	1.5	49
58	Improved performance of UVC-LEDs by combination of high-temperature annealing and epitaxially laterally overgrown AlN/sapphire. Photonics Research, 2020, 8, 589.	7.0	49
59	Study of individual grown-in and indentation-induced dislocations in GaN by defect-selective etching and transmission electron microscopy. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2001, 80, 318-321.	3.5	48
60	Electron confinement in strongly coupled GaNâˆ•AlN quantum wells. Applied Physics Letters, 2006, 88, 153113.	3.3	48
61	The discrepancies between theory and experiment in the optical emission of monolayer In(Ga)N quantum wells revisited by transmission electron microscopy. Applied Physics Letters, 2014, 104, .	3.3	48
62	Bulk single crystals of Î²-Ga2O3 and Ga-based spinels as ultra-wide bandgap transparent semiconducting oxides. Progress in Crystal Growth and Characterization of Materials, 2021, 67, 100511.	4.0	47
63	Growth, characterization, and properties of bulk SnO₂ single crystals. Physica Status Solidi (A) Applications and Materials Science, 2014, 211, 66-73.	1.8	46
64	Luminescence Related to Stacking Faults in Heterepitaxially Grown Wurtzite GaN. Materials Research Society Symposia Proceedings, 1997, 468, 293.	0.1	42
65	Optical properties of GaN epilayers and GaN/AlGaN quantum wells grown by molecular beam epitaxy on GaN(0001) single crystal substrate. Journal of Applied Physics, 2000, 88, 183-187.	2.5	42
66	Dislocation glide in {110} planes in semiconductors with diamond or zincâ€blende structure. Applied Physics Letters, 1993, 62, 2206-2208.	3.3	41
67	Effect of indium as a surfactant in (Ga_{1â€“x}In_x)₂O₃epitaxial growth onÎ²-Ga₂O₃by metal organic vapour phase epitaxy. Semiconductor Science and Technology, 2015, 30, 024013.	2.0	40
68	Stabilization of sputtered AlN/sapphire templates during high temperature annealing. Journal of Crystal Growth, 2019, 512, 142-146.	1.5	40
69	Strain-induced interface instability in GaNâˆ•AlN multiple quantum wells. Applied Physics Letters, 2007, 91, 061927.	3.3	37
70	Correlation between luminescence and compositional striations in InGaN layers grown on miscut GaN substrates. Applied Physics Letters, 2007, 91, .	3.3	37
71	A new approach to free-standing GaN using Î²-Ga2O3 as a substrate. CrystEngComm, 2012, 14, 8536.	2.6	37
72	Role of low-temperature AlGaN interlayers in thick GaN on silicon by metalorganic vapor phase epitaxy. Journal of Applied Physics, 2012, 111, .	2.5	36

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73	Intentional polarity conversion of AlN epitaxial layers by oxygen. Scientific Reports, 2018, 8, 14111.	3.3	36
74	Elastically frustrated rehybridization: Origin of chemical order and compositional limits in InGaN quantum wells. Physical Review Materials, 2018, 2, .	2.4	36
75	Dimensionality and critical sizes of GeSi on Si(100). Thin Solid Films, 1992, 216, 199-202.	1.8	35
76	Homoepitaxial seeding and growth of bulk AlN by sublimation. Journal of Crystal Growth, 2008, 310, 930-934.	1.5	35
77	Elastic and plastic relaxation in slightly undulated misfitting epitaxial layers - A quantitative approach by three-dimensional finite element calculations. Physica Status Solidi A, 1996, 156, 129-150.	1.7	33
78	Dynamics of lateral grain growth during the laser interference crystallization of a-Si. Journal of Applied Physics, 1999, 85, 4010-4023.	2.5	33
79	Effects of phase separation and decomposition on the minority carrier diffusion length in AlxGa1â^'xN films. Journal of Applied Physics, 2000, 87, 2357-2362.	2.5	33
80	Optical studies of free-standing single InGaAs/GaAs quantum dots. Semiconductor Science and Technology, 1996, 11, 1529-1533.	2.0	32
81	Impact of buffer growth on crystalline quality of GaN grown on Si(111) substrates. Physica Status Solidi (A) Applications and Materials Science, 2012, 209, 427-430.	1.8	32
82	Formation and properties of stacking faults in nitrogen-doped 4H-SiC. Physica B: Condensed Matter, 2006, 376-377, 338-341.	2.7	31
83	The transition from ripples to islands in strained heteroepitaxial growth under low driving forces. Journal of Crystal Growth, 1998, 183, 305-310.	1.5	29
84	Growth of thin AlInNâ•GaInN quantum wells for applications to high-speed intersubband devices at telecommunication wavelengths. Journal of Vacuum Science & Technology B, 2006, 24, 1505.	1.3	29
85	Analysis of statistical compositional alloy fluctuations in InGaN from aberration corrected transmission electron microscopy image series. Journal of Applied Physics, 2012, 112, .	2.5	29
86	Pyramidal-plane ordering in AlGaN alloys. Applied Physics Letters, 2003, 82, 547-549.	3.3	28
87	Atomic signatures of local environment from core-level spectroscopy in<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>Î²</mml:mi><mml:mtext>â^'</mml:mtext><mml:msub><mml:mathvariant="normal">O</mml:mi><mml:mn>3</mml:mn></mml:msub></mml:mrow></mml:math>. Physical Review B, 2016, 94, .	3.2	28
88	Melt growth and properties of bulk BaSnO₃single crystals. Journal of Physics Condensed Matter, 2017, 29, 075701.	1.8	28
89	Impact of sapphire nitridation on formation of Al-polar inversion domains in N-polar AlN epitaxial layers. Journal of Applied Physics, 2017, 122, .	2.5	28
90	Influence of magnesium doping on the structural properties of GaN layers. Journal of Crystal Growth, 1997, 181, 197-203.	1.5	27

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91	Coloration and oxygen vacancies in wide band gap oxide semiconductors: Absorption at metallic nanoparticles induced by vacancy clusteringâ€"A case study on indium oxide. Journal of Applied Physics, 2014, 115, 053504.	2.5	27
92	Impact of chamber pressure and Si-doping on the surface morphology and electrical properties of homoepitaxial (100) Î²-Ga₂O₃thin films grown by MOVPE. Journal Physics D: Applied Physics, 2021, 54, 034003.	2.8	26
93	High quality GexSi1-x by heteroepitaxial lateral overgrowth. Journal of Crystal Growth, 1992, 121, 790-794.	1.5	25
94	Microstructure, growth mechanisms and electro-optical properties of heteroepitaxial GaN layers on sapphire (0001) substrates. MRS Internet Journal of Nitride Semiconductor Research, 1996, 1, 1.	1.0	25
95	Lateral Grain Growth during the Laser Interference Crystallization of a-Si. Physica Status Solidi A, 1998, 166, 659-666.	1.7	25
96	Carrier Recombination at Screw Dislocations in n-Type AlGaN Layers. Physica Status Solidi (B): Basic Research, 1999, 216, 409-414.	1.5	25
97	Strain and composition in self-assembled SiGe islands by Raman spectroscopy. Journal of Applied Physics, 2002, 91, 6772.	2.5	25
98	The use of heater-magnet module for Czochralski growth of PV silicon crystals with quadratic cross section. Journal of Crystal Growth, 2011, 318, 249-254.	1.5	25
99	Temperatureâ€dependent electrical characterization of exfoliated Î²â€Ga₂O₃ micro flakes. Physica Status Solidi (A) Applications and Materials Science, 2014, 211, 543-549.	1.8	25
100	Control of phase formation of (Al x Ga1â€‰â^'â€‰x)2O3 thin films on c-plane Al2O3. Journal Physics D: Applied Physics, 2020, 53, 485105.	2.8	24
101	Self-assembled and ordered growth of silicon and germanium nanowires. Superlattices and Microstructures, 2009, 46, 277-285.	3.1	23
102	Influence of structural nonuniformity and nonradiative processes on the luminescence efficiency of InGaAsN quantum wells. Applied Physics Letters, 2006, 88, 011903.	3.3	22
103	SiC seed polarity-dependent bulk AlN growth under the influence of residual oxygen. Journal of Crystal Growth, 2012, 344, 19-26.	1.5	22
104	Fast homoepitaxial growth of (100) Î²-Ga2O3 thin films via MOVPE. AIP Advances, 2021, 11, .	1.3	22
105	Early growth stages of Ge0.85Si0.15 on Si(001) from Bi solution. Surface Science, 1995, 331-333, 896-901.	1.9	21
106	Dislocation Reduction in AlN and GaN Bulk Crystals Grown by HVPE. Physica Status Solidi A, 1999, 176, 453-458.	1.7	21
107	Light Confinement at Ultrasharp Metallic Tips. Japanese Journal of Applied Physics, 2008, 47, 6051.	1.5	21
108	Pyramidal inversion domain boundaries revisited. Applied Physics Letters, 2011, 99, .	3.3	21

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109	In/GaN(0001)-(3Ã—3)R30Â° adsorbate structure as a template for embedded (In, Ga)N/GaN monolayers and short-period superlattices. Applied Physics Letters, 2017, 110, .	3.3	21
110	Coherent X-Ray Scattering Phenomenon in Highly Disordered Epitaxial AlN Films. Physica Status Solidi A, 1997, 162, 529-535.	1.7	20
111	Cathodoluminescence in transmission electron microscopy. Journal of Microscopy, 2006, 224, 79-85.	1.8	20
112	Structural properties of InN films grown on O-face ZnO(0001Â¯) by plasma-assisted molecular beam epitaxy. Applied Physics Letters, 2012, 100, 152105.	3.3	20
113	Growth mechanisms in semipolar <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" altimg="si0020.gif" overflow="scroll"><mml:mo stretchy="false">(</mml:mo><mml:mn>2</mml:mn><mml:mspace width=".5em") Tj ETQq1 1 0.784314 rgBT /Overlock 10 Tf 50 587 Td <mml:	1.5	20
114	Analysis of the excitonâ€“LO-phonon coupling in single wurtzite GaN quantum dots. Physical Review B, 2015, 92, .	3.2	20
115	Single-photon emission from isolated monolayer islands of InGaN. Light: Science and Applications, 2020, 9, 159.	16.6	20
116	Diamond nucleation on silicon during bias treatment in chemical vapour deposition as analysed by electron microscopy. Diamond and Related Materials, 1997, 6, 747-751.	3.9	19
117	Compensating defects in Si-doped AlN bulk crystals. Physica B: Condensed Matter, 2007, 401-402, 323-326.	2.7	19
118	Origin of the unusually strong luminescence of<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mi>a</mml:mi></mml:math>-type screw dislocations in GaN. Physical Review B, 2014, 90, .	3.2	19
119	Interface polarization model for a 2-dimensional electron gas at the BaSnO3/LaInO3 interface. Scientific Reports, 2019, 9, 16202.	3.3	19
120	Mechanical properties and microstructural analysis of a diamond-like carbon coating on an alumina/glass composite. Journal of Materials Research, 1996, 11, 1934-1942.	2.6	18
121	Analysis of composition fluctuations in AlxGa1â^'xN. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1999, 59, 182-185.	3.5	18
122	Determination of the dislocation densities in GaN on c-oriented sapphire. MRS Internet Journal of Nitride Semiconductor Research, 1996, 1, 1.	1.0	17
123	Biâ€stable behaviour in GaNâ€based resonant tunnelling diode structures. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 431-434.	0.8	17
124	Nitride-based quantum structures and devices on modified GaN substrates. Physica Status Solidi (A) Applications and Materials Science, 2009, 206, 1130-1134.	1.8	17
125	True-Blue Nitride Laser Diodes Grown by Plasma-Assisted Molecular Beam Epitaxy. Applied Physics Express, 2012, 5, 112103.	2.4	17
126	Peculiarities of plastic relaxation of (0001) InGaN epilayers and their consequences for pseudo-substrate application. Applied Physics Letters, 2018, 113, .	3.3	17

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127	Solving the phase problem in surface crystallography: Indirect excitation via a bulk reflection. Physical Review B, 2000, 61, R16355-R16358.	3.2	16
128	Compositional Correlation and Anticorrelation in Quaternary Alloys: Competition Between Bulk Thermodynamics and Surface Kinetics. Physical Review Letters, 2007, 99, 206103.	7.8	16
129	Growth of wurtzite InN on bulk In2O3(111) wafers. Applied Physics Letters, 2012, 101, .	3.3	16
130	Stacking fault domains as sources of a-type threading dislocations in III-nitride heterostructures. Applied Physics Letters, 2016, 108, .	3.3	16
131	Comparison of the Luminous Efficiencies of Ga- and N-Polar <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mi>In</mml:mi></mml:mrow><mml:mrow><mml:mi>x</mml:mi></mml:mrow></mml:msub><mml:mo mathvariant="normal">N</mml:mi><mml:mo stretchy="false">/</mml:mo><mml:msub><mml:mrow><mml:mi>In</mml:mi></mml:mrow><mml:mrow>. Physical Review Applied, 2016, 6,	3.8	16
132	Polycrystalline Silicon on Glass Substrates for Thin Film Solar Cells. Solid State Phenomena, 1996, 51-52, 515-520.	0.3	15
133	Microstructure and growth morphology as related to electro-optical properties of heteroepitaxial wurtzite GaN on sapphire (0001) substrates. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1997, 43, 296-302.	3.5	15
134	n-type conductivity in sublimation-grown AlN bulk crystals. Physica Status Solidi - Rapid Research Letters, 2007, 1, 147-149.	2.4	15
135	Investigation on the origin of luminescence quenching in N-polar (In,Ga)N multiple quantum wells. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2013, 31, .	1.2	15
136	Plasma-assisted molecular beam epitaxy of NiO on GaN(00.1). Journal of Applied Physics, 2020, 127, .	2.5	15
137	Role of Metal Vacancies in the Mechanism of Thermal Degradation of InGaN Quantum Wells. ACS Applied Materials & Interfaces, 2021, 13, 7476-7484.	8.0	15
138	Stress Relaxation Mechanisms by Dislocations in the System Ge on Si. Solid State Phenomena, 1993, 32-33, 433-444.	0.3	14
139	Preparation and characterisation of tantalum carbide as an optional crucible material for bulk aluminium nitride crystal growth via physical vapour transport. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 1608-1612.	0.8	14
140	Investigation of interface abruptness and In content in (In,Ga)N/GaN superlattices. Journal of Applied Physics, 2016, 120, 125307.	2.5	14
141	Exciton emission of quasi-2D InGaN in GaN matrix grown by molecular beam epitaxy. Scientific Reports, 2017, 7, 46420.	3.3	14
142	Indium incorporation in homoepitaxial Î²-Ga2O3 thin films grown by metal organic vapor phase epitaxy. Journal of Applied Physics, 2019, 125, .	2.5	14
143	Approaching the high intrinsic electrical resistivity of NbO2 in epitaxially grown films. Applied Physics Letters, 2020, 116, 182103.	3.3	14
144	Mismatch relaxation by stacking fault formation of AlN islands in AlGaN/GaN structures on m-plane GaN substrates. Applied Physics Letters, 2011, 99, 061901.	3.3	13

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145	Ultraviolet laser diodes grown on semipolar (202Â¯1) GaN substrates by plasma-assisted molecular beam epitaxy. Applied Physics Letters, 2013, 102, .	3.3	13
146	Evolution of impurity incorporation during ammonothermal growth of GaN. Journal of Crystal Growth, 2016, 456, 51-57.	1.5	13
147	Large area polycrystalline silicon thin films grown by laser-induced nucleation and solid phase crystallization. Thin Solid Films, 1997, 296, 49-52.	1.8	12
148	Six-circle diffractometer for surface diffraction using an in-vacuum x-ray detector. Review of Scientific Instruments, 1999, 70, 3239-3243.	1.3	12
149	Relaxation of Misfit-Induced Strain in Semiconductor Heterostructures. Physica Status Solidi A, 1999, 171, 215-225.	1.7	12
150	Boron as an anti-surfactant in sublimation growth of AlN single crystals. Applied Physics Letters, 2006, 88, 211904.	3.3	12
151	Influence of substrate misorientation on properties of InGaN layers grown on freestanding GaN. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 1485-1487.	0.8	12
152	Surface preparation of AlN substrates. Crystal Research and Technology, 2008, 43, 651-655.	1.3	12
153	The structure of AuPd nanoalloys anchored on spherical polyelectrolyte brushes determined by X-ray absorption spectroscopy. Faraday Discussions, 2013, 162, 45.	3.2	12
154	Investigating the ranges of (meta)stable phase formation in <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:msub><mml:mrow><mml:mo>(</mml:mo><mml:mrow><mml:mn mathvariant="normal">O</mml:mi><mml:mn>3</mml:mn></mml:msub></mml:mrow. Physical Review Materials, 2020, 4, .	2.4	12
155	Role of oxygen diffusion in the dislocation reduction of epitaxial AlN on sapphire during high-temperature annealing. Journal of Applied Physics, 2021, 130, .	2.5	12
156	The driving force for dislocation multiplication in the substrate of misfitting heteroepitaxial systems. Physica Status Solidi A, 1995, 150, 453-461.	1.7	11
157	Selforganization phenomena in heteroepitaxial growth. Computational Materials Science, 1996, 7, 213-220.	3.0	11
158	Solution growth of silicon on multicrystalline Si substrate: growth velocity, defect structure and electrical activity. Journal of Crystal Growth, 1996, 166, 694-699.	1.5	11
159	Carbon nanostructures â€" Diamond nucleation centers formed during the bias pretreatment. Diamond and Related Materials, 1998, 7, 147-151.	3.9	11
160	Structure and luminescence of sol-gel synthesized anatase nanoparticles. Journal of Physics: Conference Series, 2010, 209, 012039.	0.4	11
161	Anisotropic oxidation of silicon carbide. Diamond and Related Materials, 1997, 6, 1467-1471.	3.9	10
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